

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 04-250424

(43)Date of publication of application : 07.09.1992

(51)Int.Cl. G02F 1/136
H01L 21/285
H01L 21/3205
H01L 29/40
H01L 29/784
H01L 21/336

(21)Application number : 03-001581

(71)Applicant : CANON INC

(22)Date of filing : 10.01.1991

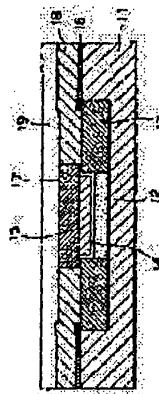
(72)Inventor : SHINDO HISASHI

(54) THIN FILM TRANSISTOR AND ITS MANUFACTURE

(57)Abstract:

PURPOSE: To realize an excellent display by embedding a metallic electric conductor in an inter-layer insulating film and forming a thin film transistor(TFT) substrate which has a flat surface, and eliminating a defect in the orientation of liquid crystal due to a step on the TFT substrate.

CONSTITUTION: A semiconductor layer 12 is embedded in an insulating substrate 11, a gate insulating film 14 is formed above the layer, and a gate electrode 15 is formed thereupon while embedded in the semiconductor layer 12. Then a thin conductive pattern 16 is formed at the place where the metallic conductor 18 is to be formed thereafter, the inter-layer insulating film 17 is deposited, and the insulating film 17 at the place of the metallic conductor 18 is removed. Then the metallic conductor 18 is formed by depositing metal selectively. Consequently, the metallic electric conductor 18 is embedded in the inter-layer insulating film 17 to realize the TFT substrate which has superior flatness and durability without having any step.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]